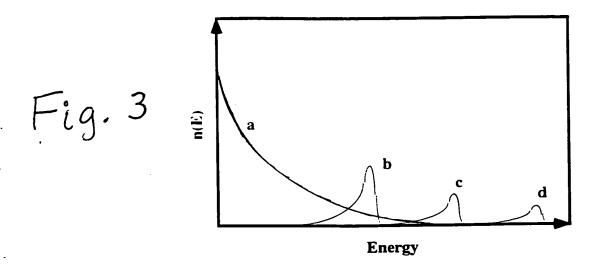
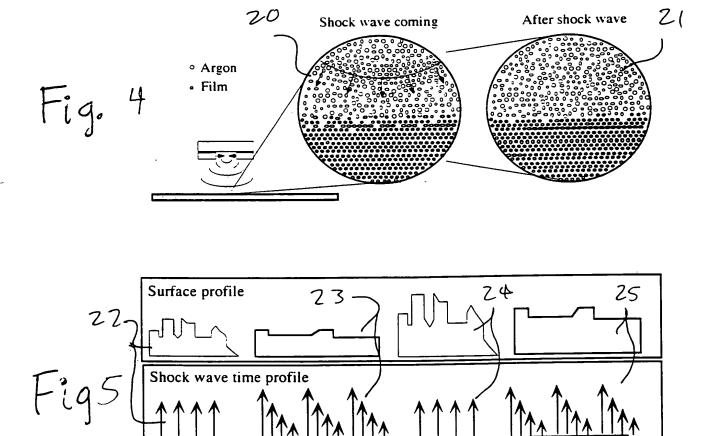


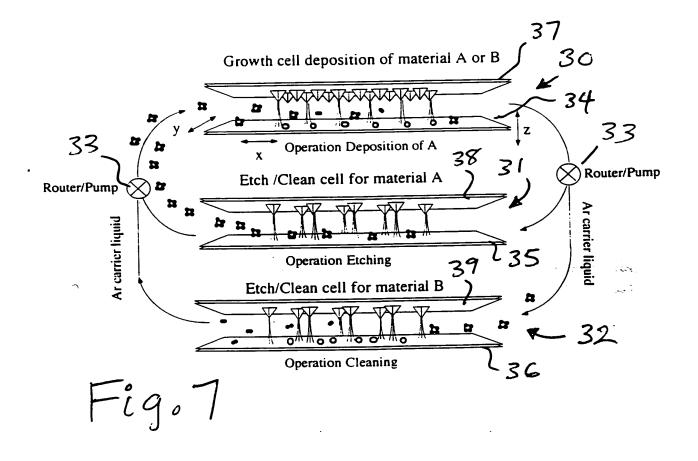
16 14 7 10 (5) 13 Discharge gap 0.1 -1μm

Fig. 6

لہ	·				C initial	Heat of	Heat
	Atomic	Melt.	Boiling	Critical	Critical		
Liquid	Number	point	point	Temp.	Pressure	Vaporisat.	Capacity
		i°KI	°K	[°K]	[Bar]	[10 <sup>3</sup> JK <sup>-1</sup> kg <sup>-1</sup> ]	[JK <sup>-1</sup> kg <sup>-1</sup> ]
Н,	1	13.8	20.3	33.3	17	310	14200
N <sub>2</sub>	7	63.0	77,4	126.2	34	200	1040
0,	8	54.8	90.2	154,6	51	213	920
F,	9	55.5	85.4	144,0	57	316	750
Ne	10	24.5	27.0	54.0	27	86	1030
Ar	18	83.8	87.3	150.8	48	158	520
Cla	17	171.6	239.1	+17,0	77	282	500
Kr	36	116.6	120	209.4	55	108	-
Xe	54	161.3	165.1	289.7	59	102	-







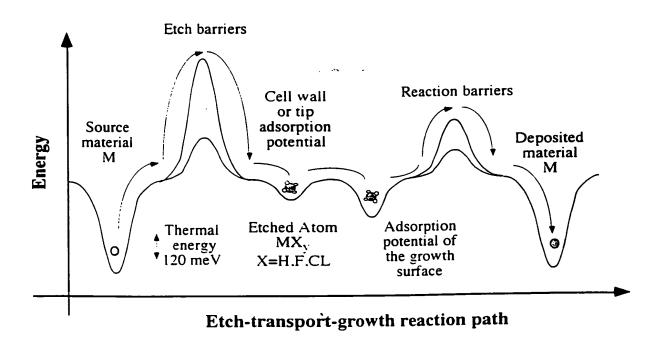
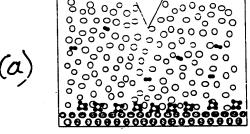
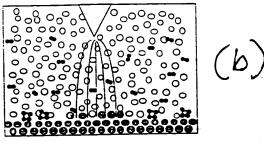


Fig. 10

## Fig. 8



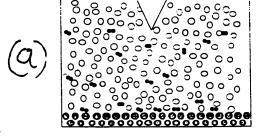
Before nanodischarge Physisorption of etched resource atom



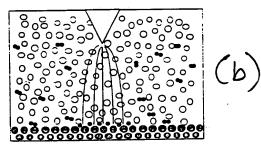
Weak nanodischarge for electron induced dissociative chemisorption of etched resource atom or deposition

Fig. 9

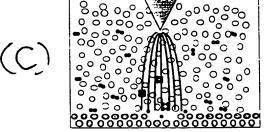
- o Argon o Resource atom 😄 Etched resource atom
- → Etchant molecule



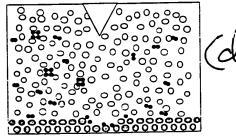
Before nanodischarge Physisorption of etchant molecules



Weak nanodischarge for electron induced dissociative chemisorption

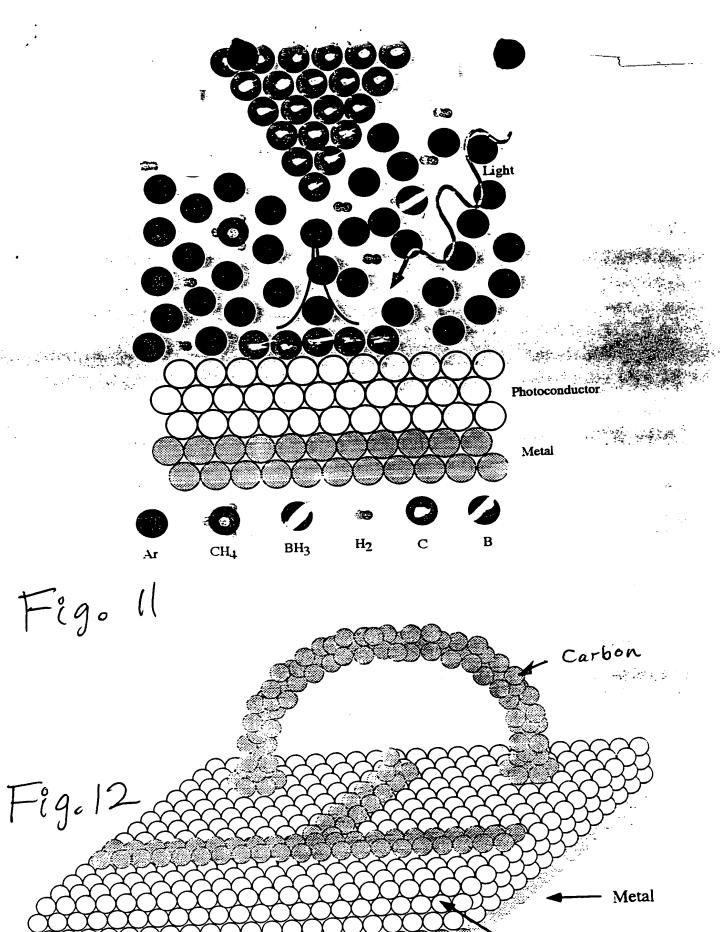


Strong nanodischarge Electron induced chemical etching



After nanodischarge re-physisorption of etchant molecules

T=80-150°K Pressure = 1.0 - 50 Bar



Photoconductor

